

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

4N35(Short), 4N36(Short), 4N37(Short)

AC LINE /DIGITAL LOGIC ISOLATOR.

DIGITAL LOGIC /DIGITAL LOGIC ISOLATOR.

TELEPHONE LINE RECEIVER.

TWISTED PAIR LINE RECEIVER.

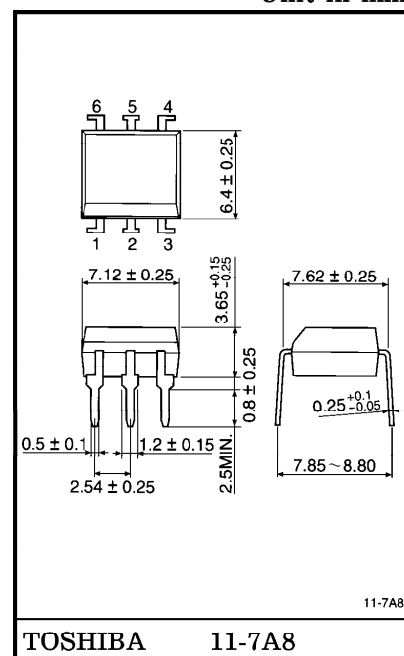
HIGH FREQUENCY POWER SUPPLY FEEDBACK CONTROL.

RELAY CONTACT MONITOR.

The TOSHIBA 4N35 (Short) through 4N37 (Short) consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a dual in-line package.

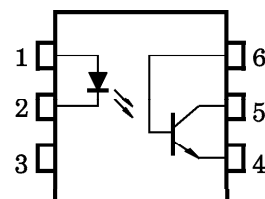
- Switching Speeds : $3\mu\text{s}$ (Typ.)
- DC Current Transfer Ratio : 100% (Min.)
- Isolation Resistance : $10^{11}\Omega$ (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

Unit in mm



Weight : 0.4g

PIN CONFIGURATIONS (Top view)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : EMITTER
- 5 : COLLECTOR
- 6 : BASE

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current (Continuous)	I_F	60	mA
	Forward Current Derating	$\Delta I_F / ^\circ\text{C}$	0.8 (*)	mA / °C
	Peak Forward Current (Note 1)	I_{PF}	3	A
	Power Dissipation	P_D	100	mW
	Power Dissipation Derating	$\Delta P_D / ^\circ\text{C}$	1.33 (*)	mW / °C
	Reverse Voltage	V_R	6	V
DETECTOR	Collector-Emitter Voltage	BV_{CEO}	30	V
	Collector-Base Voltage	BV_{CBO}	70	V
	Emitter-Collector Voltage	BV_{ECO}	7	V
	Collector Current (Continuous)	I_C	100	mA
	Power Dissipation	P_C	300	mW
	Power Dissipation Derating	$\Delta P_C / ^\circ\text{C}$	4.0 (*)	mW / °C
COUPLED	Storage Temperature	T_{stg}	-55~150	°C
	Operating Temperature	T_{opr}	-55~100	°C
	Lead Soldering Temperature (at 10s)	T_{sol}	260	°C
	Total Package Power Dissipation	P_T	300	mW
	Total Package Power Dissipation Derating	$\Delta P_T / ^\circ\text{C}$	3.3 (*)	mW / °C
	Input to Output Isolation Voltage (AC, 1 Minute)	BV_S	2500	Vrms
		4N35	2500 / 3550	Vrms / Vpk
		4N36	1750 / 2500	
		4N37	1050 / 1500	

(Note 1) Pulse width 1 μ s, 300pps

(*) Above 25°C ambient.

(**) JEDEC registered maximum BV_S , however, TOSHIBA specifies a maximum BV_S of 2500V_{rms}, 1 minute.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	0.8	1.15	1.5	V
			$I_F = 10\text{mA}$, $T_a = -55^\circ\text{C}$	0.9	—	1.7	
			$I_F = 10\text{mA}$, $T_a = 100^\circ\text{C}$	0.7	—	1.4	
	Reverse Current	I_R	$V_R = 6\text{V}$	—	—	10	μA
	Capacitance	C_D	$V = 0$, $f = 1\text{MHz}$	—	30	100	pF
DETECTOR	DC Forward Current Gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 500\mu\text{A}$	—	200	—	—
	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$	30	—	—	V
	Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$	70	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 100\mu\text{A}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 10\text{V}$	—	1	50	nA
	Collector Dark Current	I_{CEO}	$V_{CE} = 30\text{V}$, $T_a = 100^\circ\text{C}$	—	—	500	μA
	Collector-Emitter Capacitance	C_{CE}	$V = 0$, $f = 1\text{MHz}$	—	10	—	pF
COUPLED	Current Transfer Ratio		$I_F = 10\text{mA}$, $V_{CE} = 10\text{V}$	100	—	—	%
			$I_F = 10\text{mA}$, $V_{CE} = 10\text{V}$ $T_a = -55^\circ\text{C}$	40	—	—	
			$I_F = 10\text{mA}$, $V_{CE} = 10\text{V}$ $T_a = 100^\circ\text{C}$	40	—	—	
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F = 10\text{mA}$, $I_C = 0.5\text{mA}$	—	0.1	0.3	V
	Capacitance Input to Output	C_S	$V_S = 0$, $f = 1\text{MHz}$	—	0.8	2.5	pF
	Isolation Resistance	R_S	$V_S = 500\text{V}$, R. H. $\leq 60\%$	10^{11}	—	—	Ω
	Input to Output Isolation Current (Pulse Width = 8ms)	I_{IO}	$V_{iO} = 3550\text{Vpk}$	—	—	100	μA
			$V_{iO} = 2500\text{Vpk}$	—	—	100	
			$V_{iO} = 1500\text{Vpk}$	—	—	100	
	Turn-On Time	t_{ON}	$V_{CC} = 10\text{V}$, $I_C = 2\text{mA}$	—	3	10	μs
	Turn-Off Time	t_{OFF}	$R_L = 100\Omega$	—	3	10	

